

BC846, BC847, BC848

General Purpose Transistors

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	BC846	65
		BC847	45
		BC848	30
Collector-Base Voltage	V_{CBO}	BC846	80
		BC847	50
		BC848	30
Emitter-Base Voltage	V_{EBO}	BC846	6.0
		BC847	6.0
		BC848	5.0
Collector Current – Continuous	I_C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

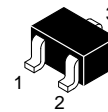
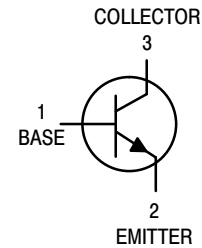
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$	P_D	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	620	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.



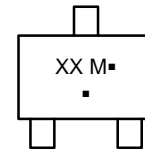
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SC-70/SOT-323
CASE 419
STYLE 3

MARKING DIAGRAM



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 12 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I _C = 10 mA)	BC846 Series BC847 Series BC848 Series	V _{(BR)CEO}	65 45 30	– – –	– – –	V
Collector–Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0)	BC846 Series BC847 Series BC848 Series	V _{(BR)CES}	80 50 30	– – –	– – –	V
Collector–Base Breakdown Voltage (I _C = 10 μA)	BC846 Series BC847 Series BC848 Series	V _{(BR)CBO}	80 50 30	– – –	– – –	V
Emitter–Base Breakdown Voltage (I _E = 1.0 μA)	BC846 Series BC847 Series BC848 Series	V _{(BR)EBO}	6.0 6.0 5.0	– – –	– – –	V
Collector Cutoff Current (V _{CB} = 30 V)	(V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	– –	– –	15 5.0	nA μA

ON CHARACTERISTICS

DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h _{FE}	– – –	90 150 270	– – –	–
(I _C = 2.0 mA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C		110 200 420	180 290 520	220 450 800	
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{CE(sat)}	– –	– –	0.25 0.6	V
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{BE(sat)}	– –	0.7 0.9	– –	V
Base–Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		V _{BE(on)}	580 –	660 –	700 770	mV

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	–	–	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	–	–	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	–	–	10	dB

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BC846A, BC847A, BC848A



Figure 1. DC Current Gain vs. Collector Current



Figure 2. DC Current Gain vs. Collector Current

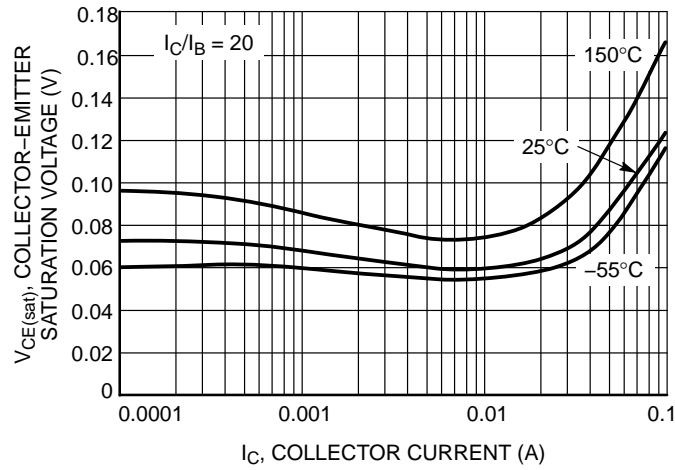


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current



Figure 4. Base-Emitter Saturation Voltage vs. Collector Current

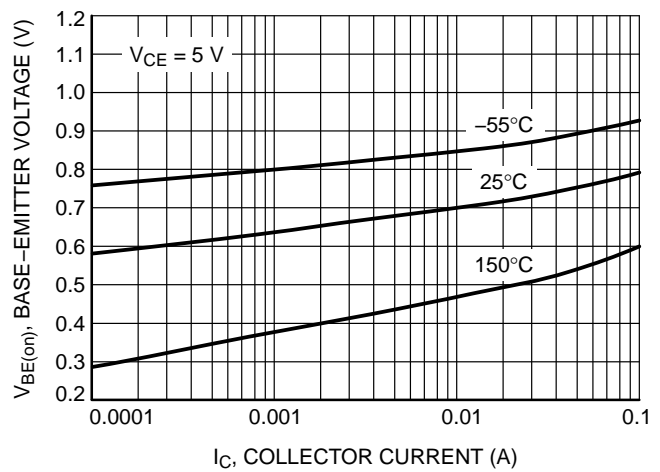


Figure 5. Base-Emitter Voltage vs. Collector Current

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BC846A, BC847A, BC848A



Figure 6. Collector Saturation Region



Figure 7. Base-Emitter Temperature Coefficient



Figure 8. Capacitances



Figure 9. Current-Gain - Bandwidth Product

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BC846B



Figure 10. DC Current Gain vs. Collector Current



Figure 11. DC Current Gain vs. Collector Current



Figure 12. Collector Emitter Saturation Voltage vs. Collector Current



Figure 13. Base Emitter Saturation Voltage vs. Collector Current



Figure 14. Base Emitter Voltage vs. Collector Current

BC846B

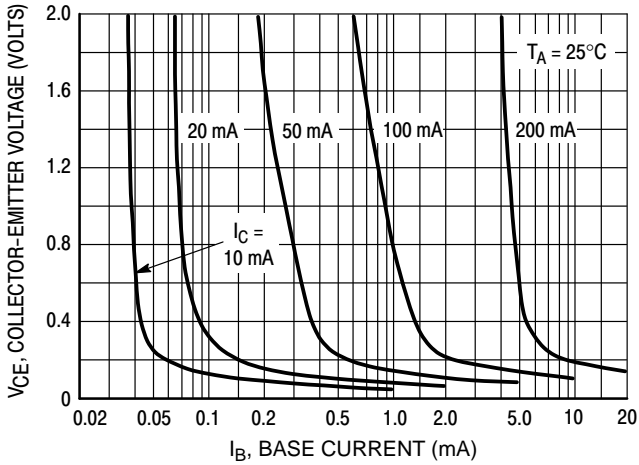


Figure 15. Collector Saturation Region

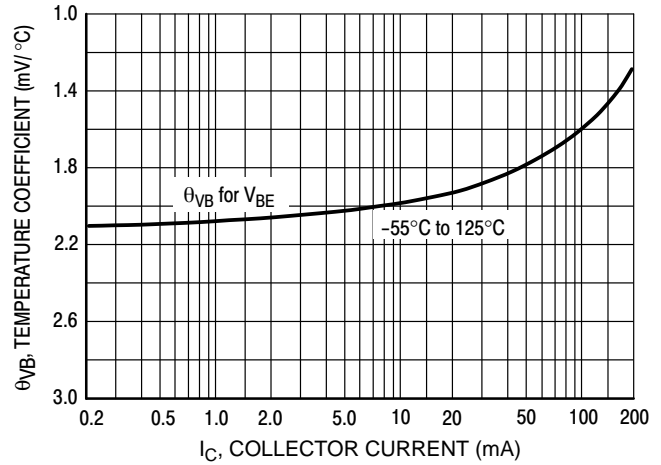


Figure 16. Base-Emitter Temperature Coefficient

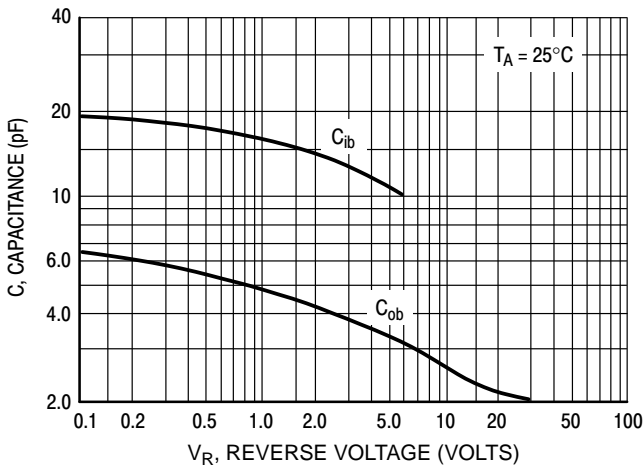


Figure 17. Capacitance



Figure 18. Current-Gain - Bandwidth Product

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BC847B, BC848B

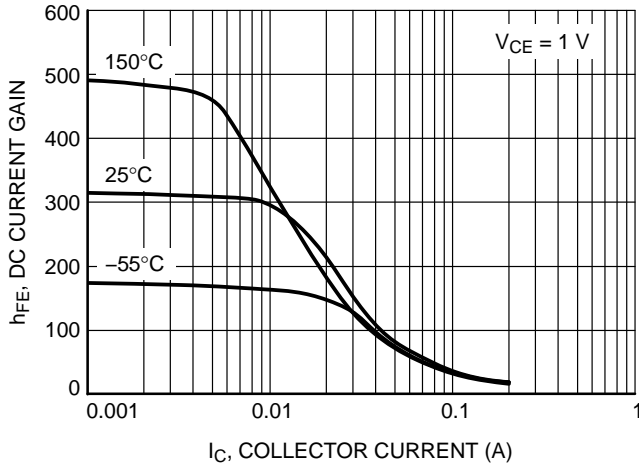


Figure 19. DC Current Gain vs. Collector Current

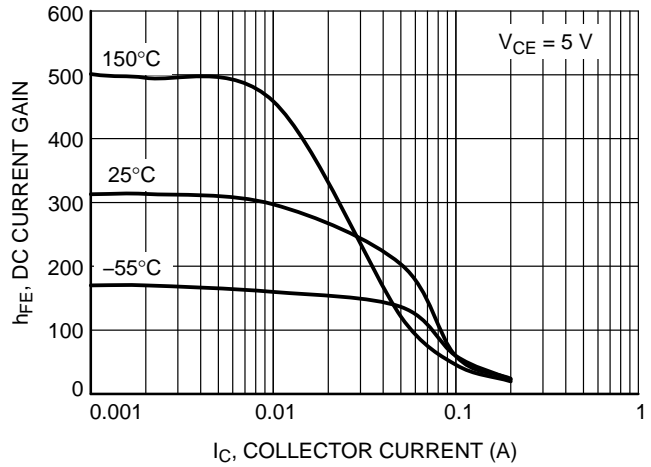


Figure 20. DC Current Gain vs. Collector Current

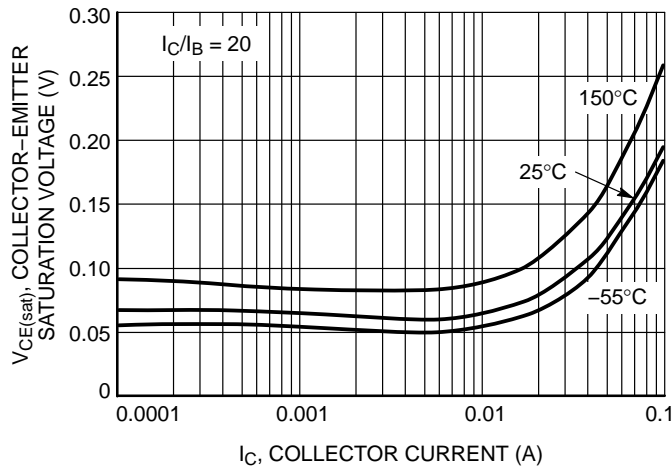


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current

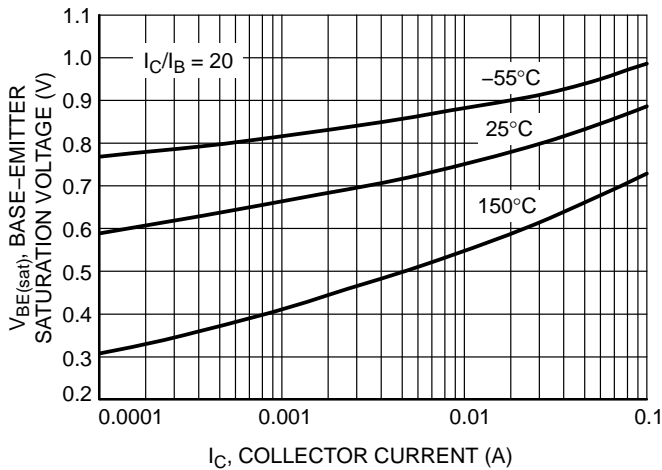


Figure 22. Base Emitter Saturation Voltage vs. Collector Current

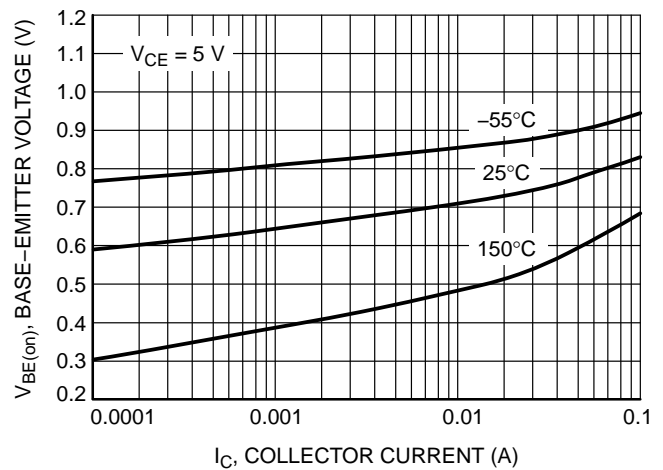


Figure 23. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847B, BC848B

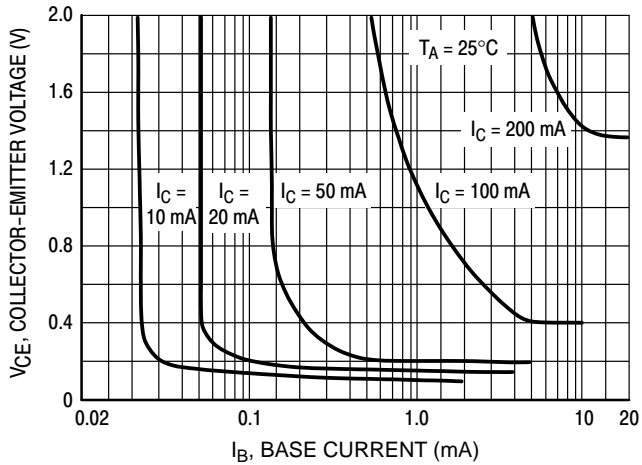


Figure 24. Collector Saturation Region

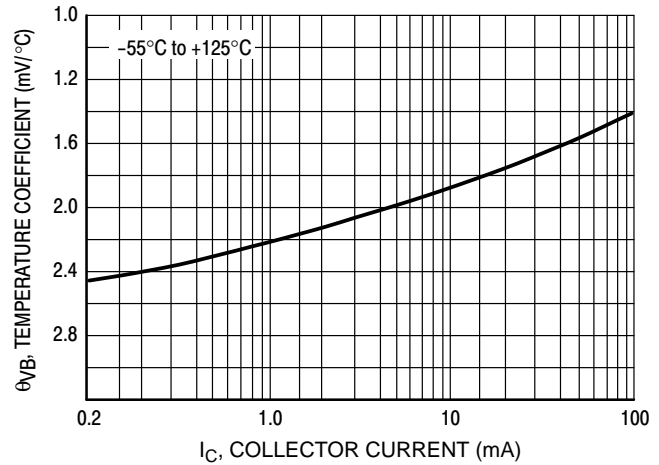


Figure 25. Base-Emitter Temperature Coefficient

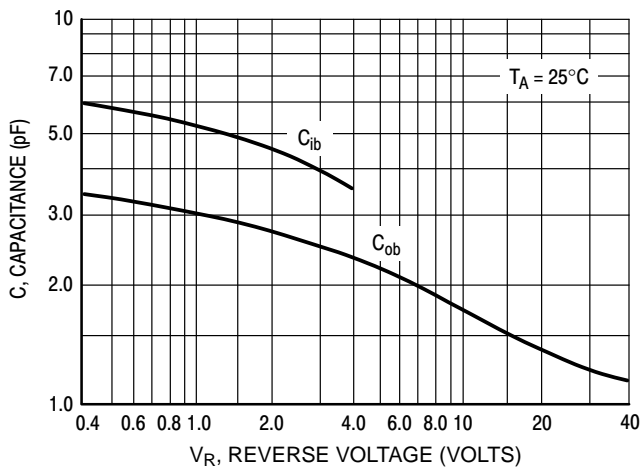


Figure 26. Capacitances

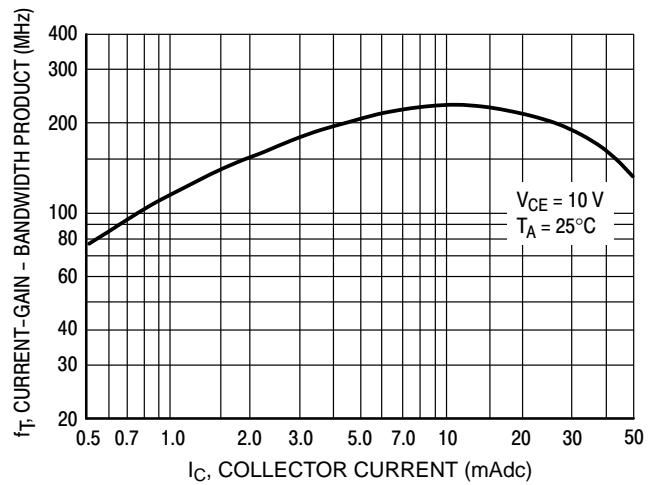


Figure 27. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC847C, BC848C

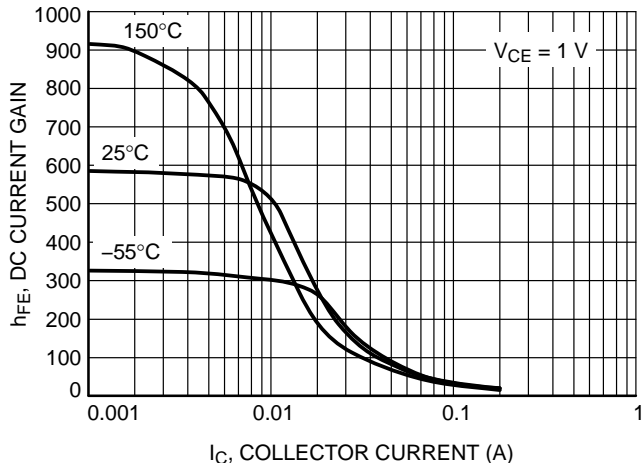


Figure 28. DC Current Gain vs. Collector Current

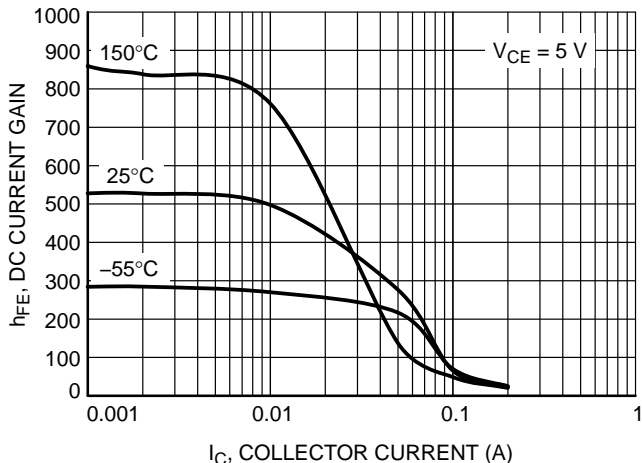


Figure 29. DC Current Gain vs. Collector Current

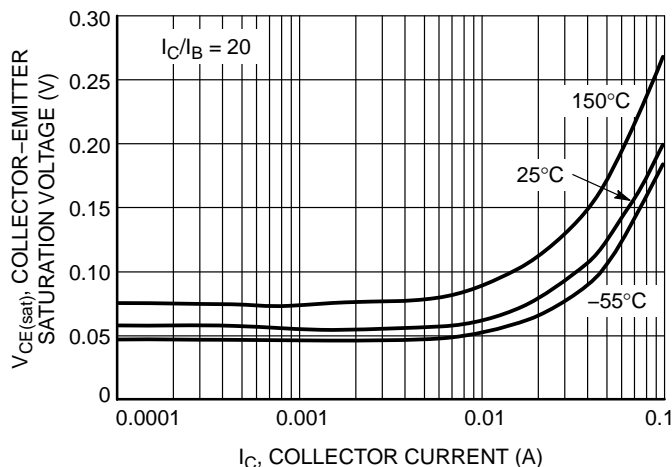


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

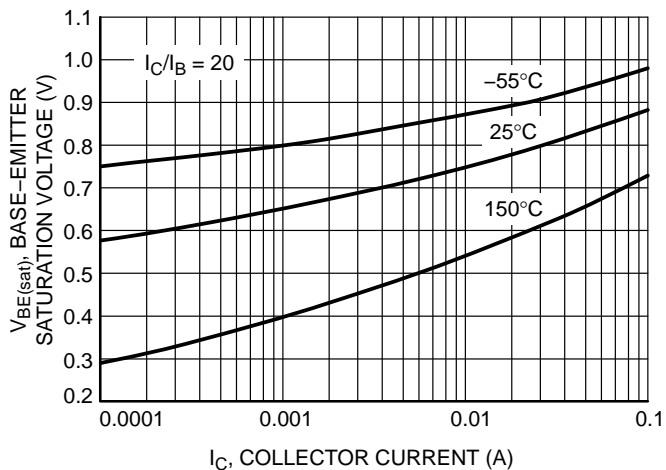


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

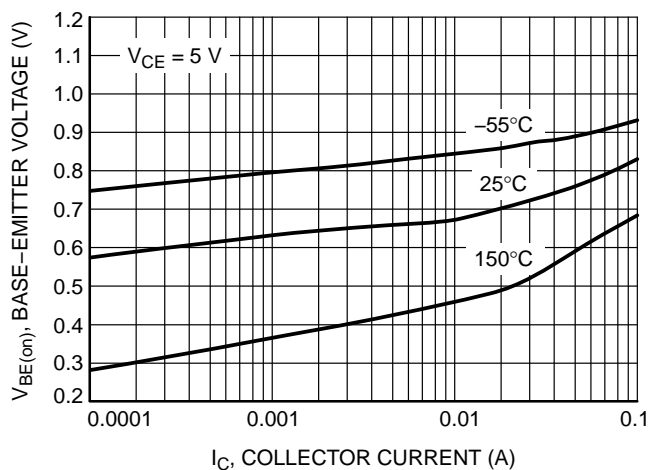


Figure 32. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847C, BC848C

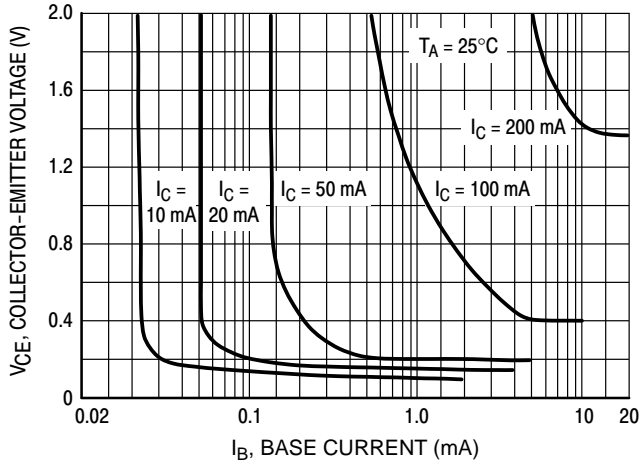


Figure 33. Collector Saturation Region

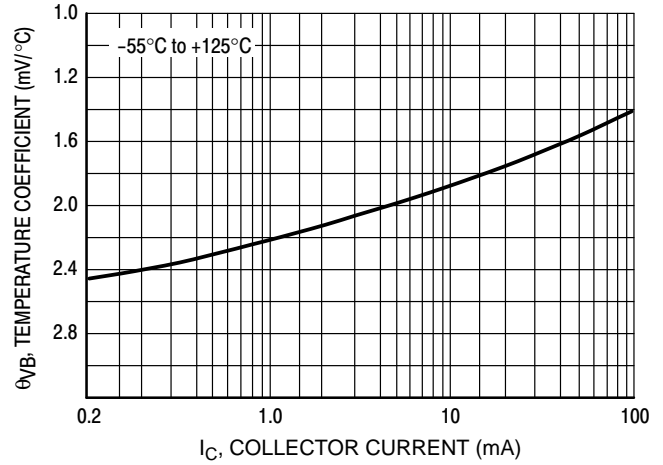


Figure 34. Base-Emitter Temperature Coefficient

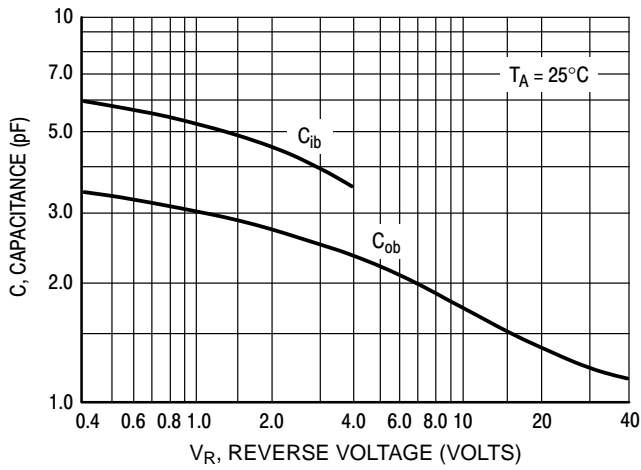


Figure 35. Capacitances

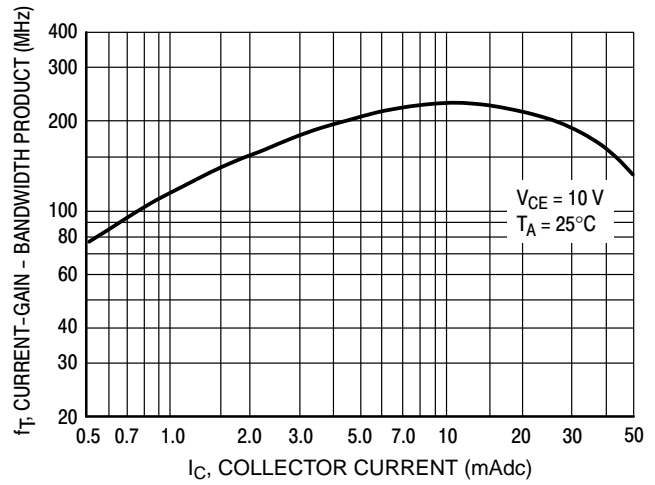


Figure 36. Current-Gain - Bandwidth Product

BC846, BC847, BC848



Figure 37. Safe Operating Area for BC846A, BC846B

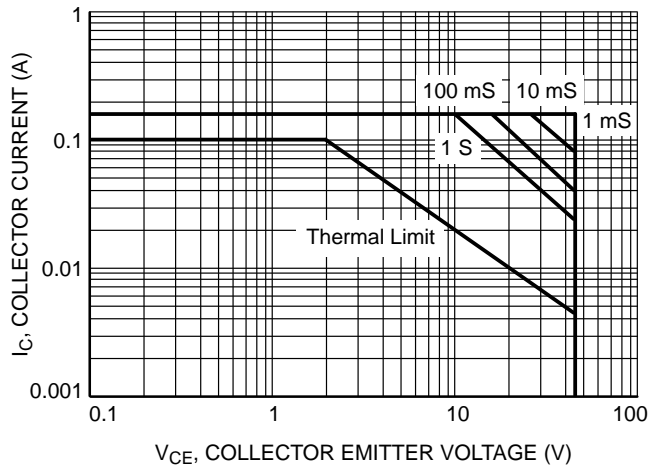


Figure 38. Safe Operating Area for BC847A, BC847B, BC847C

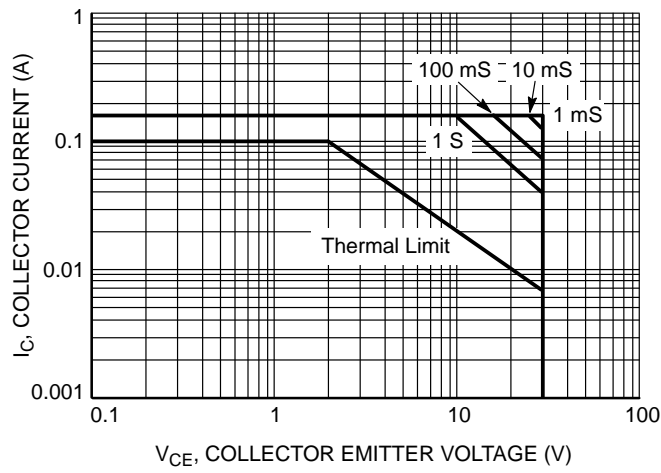


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C

BC846, BC847, BC848

DEVICE ORDERING AND SPECIFIC MARKING INFORMATION

Device	Specific Marking Code	Package	Shipping†
BC846BWT1G	1B	SC-70 (SOT-323) (Pb-Free)	3,000 / Tape & Reel
SBC846BWT1G*			
BC847AWT1G	1E		3,000 / Tape & Reel
SBC847AWT1G*			
BC847BWT1G	1F		3,000 / Tape & Reel
SBC847BWT1G*			
BC847CWT1G	1G		3,000 / Tape & Reel
SBC847CWT1G*			
BC847CWT3G	1G		10,000 / Tape & Reel
SBC847CWT3G*			
BC848BWT1G	1K		3,000 / Tape & Reel
NSVBC848BWT1G*			
BC848CWT1G	1L		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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单击下面可查看定价，库存，交付和生命周期等信息

[>>ON Semiconductor\(安森美\)](#)